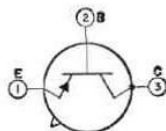


2N705

TRANSISTOR

Germanium p-n-p type used in high-speed logic-circuit applications in data-processing equipment. JEDEC No. TO-18 package; outline 12, Outlines Section.



MAXIMUM RATINGS

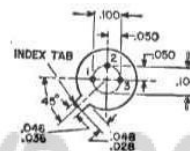
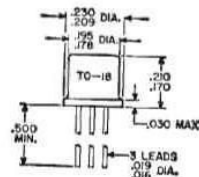
Collector-to-Base Voltage (with emitter open)	-15 max	volts
Collector-to-Emitter Voltage (with external base-to-emitter resistance = 10 ohms or less) ..	-15 max	volts
Emitter-to-Base Voltage (with collector open)	-3.5 max	volts
Collector Current	-50 max	ma
Emitter Current	50 max	ma
Transistor Dissipation:		
At ambient temperatures up to 25°C	150 max	mw
At case temperatures up to 25°C	300 max	mw
At ambient or case temperatures above 25°C	See curve	page 80
Temperature Range:		
Operating (junction) and storage	-65 to 100	°C
Lead Temperature (for 10 seconds maximum)	230 max	°C

CHARACTERISTICS

Base-to-Emitter Voltage (with collector ma = -10 and base ma = -0.4)	-0.44 max	volt
Collector-to-Emitter Saturation Voltage (with collector ma = -10 and base ma = -0.4)	-0.3 max	volt
Collector-Cutoff Current (with collector-to-base volts = -5 and emitter current = 0)	-3 max	µa
Collector Transition Capacitance (with collector-to-base volts = -10, emitter current = 0, and frequency = 1 Mc)	5	pf
Emitter Transition Capacitance (with emitter-to-base volts = -2, collector current = 0, and frequency = 1 Mc)	3.5	pf

In Common-Emitter Circuit

Small-Signal Forward Current-Transfer Ratio (with collector- to-emitter volts = -5, collector ma = -10, and frequency = 100 Mc)	3
DC Forward Current-Transfer Ratio (with collector-to-emitter volts = -0.3 and collector ma = -10)	25 min



-12-